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Photoluminescence from voids created by femtosecond laser pulses inside cubic-BN

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Photoluminescence (PL) from femtosecond laser modified regions inside cubic-boron nitride (c-BN) was measured under UV and visible light excitation. Bright PL at the red spectral range was observed, with a typical excited state lifetime of $\sim$ 4 ns. Sharp emission lines are consistent with PL of intrinsic vibronic defects linked to the nitrogen vacancy formation (via Frenkel pair) observed earlier in high energy electron irradiated and ion-implanted c-BN. These, formerly known as the radiation centers, RC1, RC2, and RC3 have been identified at the locus of the voids formed by single fs-laser pulse. The method is promising to engineer color centers in c-BN for photonic applications.

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Investigation of high pressure and temperature phases of different materials are spanning from the fundamental research[1–3] as a recently demonstrated metallic bonding in hydrogen[4] to developing new pathways of material synthesis for future practical use[5]. Structural modifications inside transparent materials can be controlled down to sub-wavelength resolution[6,7] by direct laser write and opens possibility to create micro-optical[8] and mechanical[9] elements, waveguides[10–12], to render a chemically resistant material wet-bath etchable for microfluidic applications[13]. Of a particular interest are wide band gap materials, such as Cubic BN (c-BN) with a bulk modulus of $\sim$ 400 GPa and a wide bandgap of 6.5 eV. It is made by the diamond anvil cell (DAC) or belt-type high pressure compression of a hexagonal phase h-BN[14].

Optical properties of boron nitrides are attracting an increasing interest due to their ability to host optically stable single photon emitters at room temperature[15] and their hyperbolic properties. To this extent, sub-bandgap excitation of controllably formed and patterned defects in c-BN is strongly anticipated. Moreover, theoretical modeling predicts an analog of the nitrogen-vacancy NV^- centers known in diamond for the B-vacancy oxygen pair in c-BN[16], which is yet to be confirmed experimentally. The stacking fault energy 191 ± 15 mJ.m^{-2} in c-BN is comparable to that in diamond[17] and a similar defect formation is expected.

Here, we employ a femtosecond (fs)-laser irradiation technique[18,19] to create optically active color centers in c-BN. Using confocal microscopy and time resolved measurements, we show that the formed voids are extremely bright PL sources and originates from the N-vacancy related radiation center RC-defects[20] observed earlier in c-BN only by high energy particle or ionising radiation exposure[21].

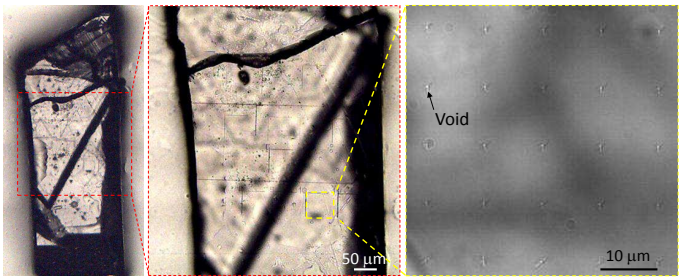

FIG. 1. Sample of c-BN crystal and close up views of the laser structured regions. The left image shows array fabricated by $E_p = 27$ nJ energy pulses at 515 nm wavelength focused with an objective lens of numerical aperture $NA = 1.42$ at depth of ~ 10 μm; pulse duration was 230 fs.

Samples of c-BN were grown on a belt-type high pressure equipment[14] and were used for experiments of void formation by single femtosecond (fs-)laser pulses tens of micrometers below the surface (Fig. 1).

Laser pulses of $\tau_p = 230$ fs duration at fundamental $\lambda = 1030$ nm and second harmonic 515 nm wavelengths were focused at a $10-20$ μm depth below the surface of a facet plane inside c-BN crystals (Fig. 1). Tight focusing with numerical aperture $NA = 1.42$ was implemented to form arrays of damage sites recorded at different pulse energies E_p at a single pulse conditions. Separation between irradiation spots was 10 μm to eliminate a cross talk for void-formation and optical characterization. For comparison, dense array of ablation patterns were fabri-

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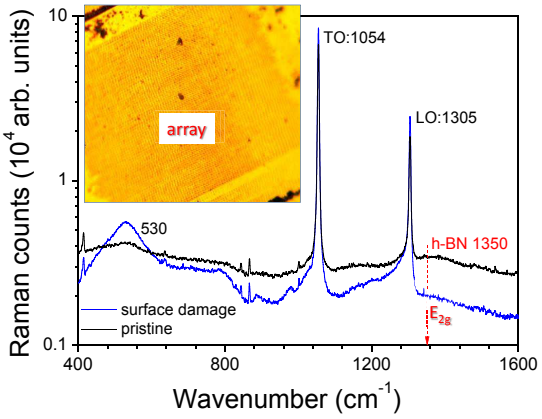

FIG. 2. Raman spectra of surface ablation array recorded with 800 nm/150 fs pulses. Excitation wavelength of Raman scattering was 785 nm. Inset shows field of view approximately 0.1×0.1 mm^2.

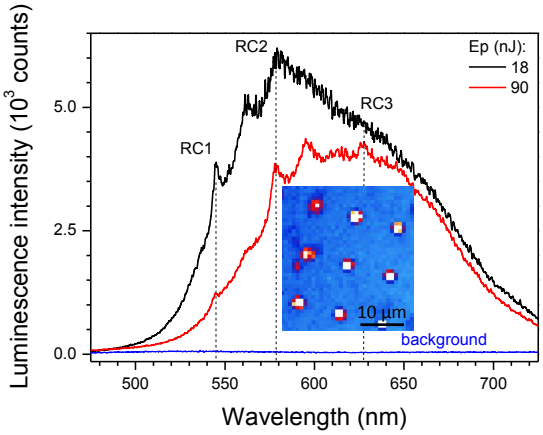

FIG. 3. Photoluminescence (PL) spectra from void-structures in c-BN. PL excitation wavelength was 405 nm. The inset: a PL map under 532 nm excitation; the void-structures were made with $E_p = 18$ nJ single pulses of 515 nm wavelength at a 10 μm depth.

cated with 800 nm/150 fs pulses focused with $NA = 0.95$ on the surface of c-BN. Judgement of the void presence at the center of irradiated spot inside c-BN was made by a sharp optical contrast change which was identical to the void formation in crystalline sapphire, quartz and glasses of different refractive indices[22,23]; focused ion milling will be implemented next to reveal an internal structure of the void as it was made for voids at the Si-SiO_2 interface[24].

Photoluminescence and its transients were measured under laser diode 405 nm/30 ps or 510 nm/100 ps (PiLAS; advanced Laser Diode systems) excitation using $NA = 0.7$ objective lens and a single photon counting avalanche photo diode (SPCM-AQRH-14) as a detector. A spectral window of PL collection was filter selected at 620-650 nm. A piezo-scanner was implemented to record a PL map around the void-structures. PL spectra were recorded by a spectrometer (Princeton Instruments). Raman spectra were acquired with an InVia Streamline microscope (Renishaw, UK) under 785 nm excitation and $NA = 0.4$ focusing.

Strong optical contrast changes were observed at the focus of tightly focused $NA = 1.42$ fs-laser pulse in c-BN at the threshold values of $E_p = 4.5$ nJ ($\lambda = 515$ nm) and 80 nJ (1030 nm) estimated. Due to high refractive index of $n \simeq 2.1$[25] at the used wavelength, a spherical aberration defines the focal volume which became slightly larger[26] as compared with the diffraction-limited focal size of diameter $d = 1.22\lambda/NA$. At such tight focusing, a self focusing is avoided since 10 nJ pulse corresponds to only 43 kW/pulse power but reach 7.1 TW/cm^2 irradiance for $\lambda = 1030$ nm. These are direct write conditions with irradiance of ~ 10 TW/cm^2 when voids are formed in different transparent materials under equivalent focusing[22,23]. The voids are of sub-wavelength $50 - 200$ nm in diameters[22,23] and their actual size has to be measured using focused ion beam cross sections. Micro-cracks comparable in size with the central void-structure were observed in c-BN when the void-structure was created by a single focused fs-laser pulse (Fig. 1). These strongly modified regions were subject of further examination using PL (Fig. 3).

When void is formed in c-BN it could be expected that relaxation into a less dense phase of h-BN or into an amorphous phase occurs. To test this conjecture an ablation on the surface was carried out and Raman scattering measured. Characteristic transversal and longitudinal optical phonon modes TO and LO, respectively, were observed with small broadening at the high-energy side of the modes. Back-scattered Raman signal excited by 785 nm irradiation was collected with a $NA = 0.4$ lens averaging response from area with several ablation sites made by single pulses. Wide peak at 520 cm^{-1} (65.7 meV) was the strongest modification observed from surface ablated regions made by 800 nm/150 fs pulses. Presence of a lower density h-BN was not confirmed from ablated regions which would be recognisable by its 1350 cm^{-1} E_{2g} mode[27]. Widening of the Raman peak at the LO and TO modes could be related to disordering at the void region, however there is no obvious shift to smaller wavenumbers which takes place for nanocrystallites of c-BN[28].

Confocal microscopy with 405 nm excitation source was employed to characterize the fabricated voids-structures in c-BN. Photoluminescence of nitrogen is well studied in atmospheric discharge experiments and lightning observations with lines at deep-UV and at 455, 556, 577 nm identified as atomic neutral nitrogen N[29]. Under 405 nm illumination, PL from the void regions has recognizable features within similar spectral range (Fig. 3). Molecular N_2 PL which occurs in 300-400 nm window was out of the range of observation in this first experiment. The confocal map is shown in inset of Fig. 3. The bright spots correspond to the location of the voids.

The observed PL features are matching perfectly the

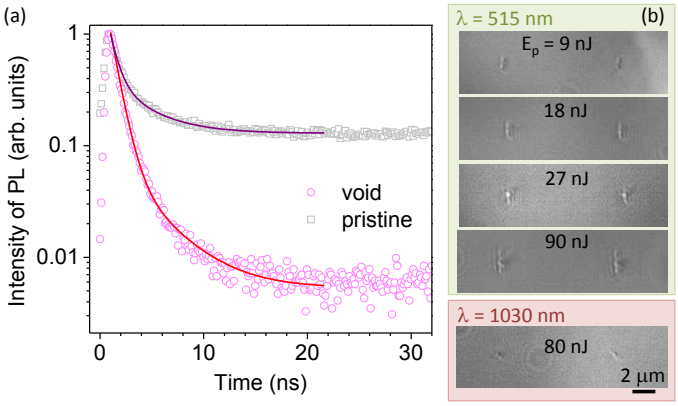

FIG. 4. (a) Photoluminescence (PL) transients from the void structure and from undamaged c-BN excited by 510 nm/100 ps illuminaiton using objective lens $NA = 0.7$. Void was formed by $E_p = 27$ nJ single pulses of 515 nm wavelength at a 10 μm depth. (b) Optical images of the typical laser damaged sites with void present at the center for the brightest central spot; void-structures made at different pulse energies E_p and 515 and 1030 nm wavelength.

TABLE I. Emission of RC centers created by electron and photon irradiation.

Defect Radiation Center (RC)	CL [nm] 4.5 MeV electrons[21]	PL [nm] fs-laser pulse (this study)
RC1	546.2	542 ± 2
RC2	576.7	578 ± 2
RC3	623.1	628 ± 2

intrinsic vibronic defects RC1,2,3 reported in c-BN irradiated by high energy 1.9 MeV electrons[20,21]. It is noteworthy that PL was measured at room temperature and no post-irradiation annealing was required as it is usually the case after ion implantation. The intrinsic Frenkel pair defects due to the N-vacancy formation earlier observed in cathodo-luminescence (CL) and identified as RC1 with zero phonon line of (2.27 eV, 546.2 nm), RC2 (2.15 eV, 576.7 nm) and RC3 (1.99 eV, 623.1 nm)[20,21] were found matching very well the defect PL we observed from the voids made by fs-laser pulses (see, Table I). Deterministic fabrication of these color centesr is demonstrated here for the first time using ultra short light pulses.

The PL excited at 510 nm/100 ps illumination showed close to a single exponential decay with time constant of 3.7 ns (Fig. 4(a)), while under the 405 nm/30 ps excitation the decay was also similar 4 ns (not shown). Long stretched exponential decay is usually indicative of a recombination of the electrons and holes trapped on defects which are distributed in energy and separated spatially by varying distances. Very long multi-exponential decays were observed in silica glass with nano-gratings formed by fs-laser irradiation as measured by a time-domain method[30]. Very similar temporal transients from pristine regions and void-structures are consistent with self-trapping of electron-hole pairs (a pathway of excitonic decay) which is typical for wide bandgap materials. Such scenario is also consistent with stretched exponential decay and is observed in pristine regions of crystals and dielectrics.

The RC2 and RC3 centers were observed in CL under 3.5 GPa pressure[20]. Following earlier studies of void-structures in sapphire and silica[24,31] even higher residual pressure were observed at the void region. Future studies are required to reveal internal morphology of the voids in c-BN, presence of amorphisation with better spatial resolution. Small changes of the Raman TO and LO phonon modes from ablated regions as well as ± 5 nm changes in PL of the RC-defects might de related to presence of shock amorphised c-BN as it was observed in sapphire[32] where voids had shell of metastable amorphous phase.

Void-formation in c-BN by single fs-laser pulses was observed by strong optical contrast changes at tens - of - micrometers below the surface. Three vibronic radiation center defects RC1,2,3 were identified in c-BN by photon irradiation. PL from single voids showed fast ~ 4 ns transient with stretched exponential slower tail of the decay. Photoluminescence transients from regions with defects and without were fitted by the same time constants. This corroborates an intrinsic character of the Frenkel pair defects as they are, most probably, formed from the same pre-cursors which active in self-trapping of photo-carriers in pristine c-BN. There were no indication of h-BN formation on the surface nor in the bulk from laser treated volume. Laser patterning of defects in wide bandgap materials with sub-wavelength precision and a 3D capability of their patterning is appealing for engineering of deterministic sources for photonics in BN systems.

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